# MSKSEMI















**ESD** 

TVS

TSS

MOV

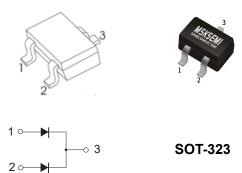
**GDT** 

**PLED** 

# Brodnet data speet

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## **BAV70W** switching DIODE

#### **FEATURES**

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

**MARKING: KJA** 

### Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$		
Working Peak Reverse Voltage	$V_{RWM}$	75	V
DC Blocking Voltage	V <sub>R</sub>		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I <sub>FM</sub>	300	mA
Average Rectified Output Current	Io	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I <sub>FSM</sub>	2.0	Α
Power Dissipation	Pd	200	mW
Thermal Resistance Junction to Ambient	$R_{ heta JA}$	625	°C/W
Junction Temperature	Tj	150	$^{\circ}\!\mathbb{C}$
Storage Temperature	T <sub>STG</sub>	-55~+150	$^{\circ}\!\mathbb{C}$

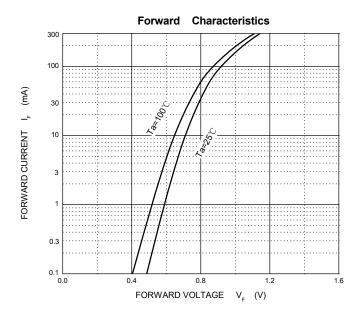
### Electrical Ratings @Ta=25℃

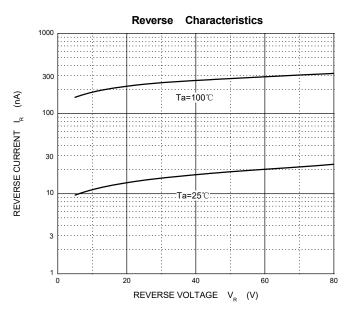
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Reverse breakdown voltage	V <sub>(BR)</sub>	75			V	I <sub>R</sub> =100μA
	$V_{F1}$			0.715	V	I <sub>F</sub> =1mA
Forward voltage	$V_{F2}$			0.855	V	I <sub>F</sub> =10mA
	V <sub>F3</sub>			1.0	V	I <sub>F</sub> =50mA
	V <sub>F4</sub>			1.25	V	I <sub>F</sub> =150mA
Reverse current	I <sub>R1</sub>			2.5	μΑ	V <sub>R</sub> =75V
Reverse current	I <sub>R2</sub>			25	nA	V <sub>R</sub> =20V
Capacitance between terminals	C <sub>T</sub>			2	pF	V <sub>R</sub> =0V,f=1MHz
Boyorga racovery time	t <sub>rr</sub>			4	ns	I <sub>F</sub> =I <sub>R</sub> =10mA
Reverse recovery time						Irr=0.1 $XI_R$ , $R_L$ =100 $\Omega$

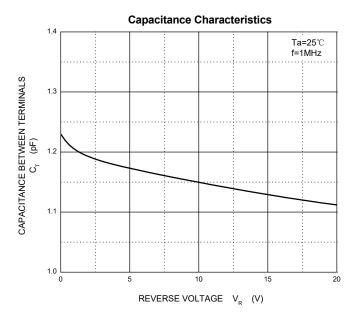


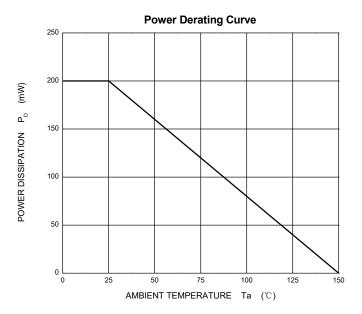
#### Semiconductor

### **Typical Characteristics**



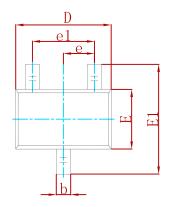


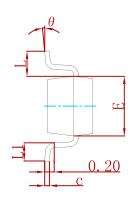


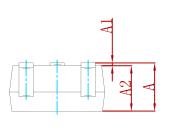




#### **PACKAGE MECHANICAL DATA**

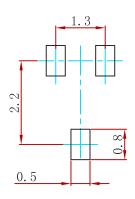






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650	) TYP	0.026	TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BAV70W	SOT-323	3000





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